

**Amendments to the Specification**

Please replace the figure caption for Fig. 9 on page 3, paragraph 17, with the following rewritten figure caption:

Fig. 9 is a flow chart of a method of manufacturing a storage device according to an embodiment of this invention;

Please replace the paragraph [0021] beginning on page 4, and ending on page 5, with the following paragraph:

Memory storage device 100 further includes charge trapping structure 140 that is disposed on a portion of second semiconducting layer 124. In addition, memory storage device 100 also includes conductive gate tip 150 disposed over charge trapping structure 140. Conductive gate tip 150, in this embodiment, is a metal or semiconductor tip formed utilizing a wide variety of metals or semiconductors such as tungsten, gold, platinum, palladium, rhenium, tantalum, silicon, gallium arsenide, or cadmium sulfide to name just a few materials that may be used. In alternate embodiments, as shown in an expanded cross-sectional view in Fig. 1b, conductive gate tip 150' may include base 152 and outer layer 153 disposed or formed on the outer surface of base 152. In one embodiment, base 152 may be formed utilizing any conductive material that provides sufficient conductivity to either generate a data bit or read a data bit such as a metal, a doped semiconductor, or an organic conductor. Outer layer 153 may be formed utilizing from any dielectric or electrically insulating layer. Examples of such dielectric materials that may be utilized include, but are not limited to, oxides, nitrides, carbides, borides as well as organic and polymeric dielectric layers. In a second embodiment, both base 152 and outer layer 153 may be formed utilizing a conductor as described above. For example, base 152 may be formed utilizing one metal such as aluminum, titanium, copper, or tungsten, and outer layer 153 may be formed utilizing a different metal such as gold, platinum, or palladium. In still other embodiments, base 152

may be formed utilizing a dielectric material such as silicon oxide or silicon nitride to name just a couple of examples of the wide range dielectric materials, including high dielectric constant materials, that may be used. Outer layer 153, in this embodiment, may be formed over the dielectric material forming base 152 utilizing any conductive material that provides sufficient conductivity to either generate a data bit or read a data bit. ~~In still other embodiments, base 152.~~ In addition, conductive gate tip 150 and 150' may be formed in a wide variety of shapes, for example, what is generally referred to as a "Spindt" tip may be used, or a trapezoidal shaped atomic force microscope tip formed at the end of a cantilever also may be utilized. Generally, the end of the tip closest to the charge trapping structure will be anywhere from a few atoms to a few nanometers in size. In addition, the particular shape of the conductive gate tip will depend on the desired field generated between the conductive gate tip and second semiconducting layer 124 to produce the desired shape and size of the charged bit formed in the charge trapping structure.

Please replace the paragraph [0045] beginning on page 19, and ending on page 20, with the following paragraph:

Conductive gate mounting process 998 is utilized to package or assemble a conductive gate support, a moving layer support and drive support together to form a frame that encloses the conductive gates and charge trapping storage structure. Generally, the moving layer support is connected to a micromover that is mechanically suspended between the conductive gate support and the drive support. In this manner at least one conductive gate is disposed over the charge trapping structure. In addition, either the conductive gate tip or the charge trapping structure moves relative to the other. Typically conductive gate mounting process 998 includes creating a micromover that is coupled to either the conductive gates or to the charge trapping storage structure depending on which structure is to move relative to the other. The micromover may be formed to move in one, two, or three dimensions.